











CSD19532KTT

SLPS553 - OCTOBER 2015

CSD19532KTT 100 V N-Channel NexFET™ Power MOSFET

Features

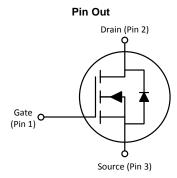
- Ultra-Low Qa and Qad
- Low Thermal Resistance
- Avalanche Rated
- Pb-Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- D²PAK Plastic Package

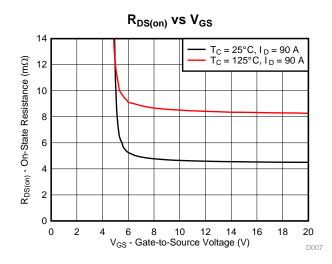
Applications

- Secondary Side Synchronous Rectifier
- Hot Swap
- Motor Control

Description 3

This 100 V, 4.6 m Ω , D²PAK (TO-263) NexFETTM power MOSFET is designed to minimize losses in power conversion applications.





Product Summary

T _A = 25°	С	TYPICAL VA	UNIT		
V_{DS}	Drain-to-Source Voltage 100				
Q_g	Gate Charge Total (10 V)		nC		
Q _{gd}	Gate Charge Gate to Drain	5.6	nC		
0	Drain-to-Source On Resistance	V _{GS} = 6 V	5.3	mΩ	
R _{DS(on)}	Diam-to-Source On Resistance	V _{GS} = 10 V 4.6		mΩ	
V _{GS(th)}	Threshold Voltage	2.6		V	

Ordering Information⁽¹⁾

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD19532KTT	500	13-Inch	D ² DAK Disatis Dasks	Tape &
CSD19532KTTT	50	Reel	D ² PAK Plastic Package	Reel

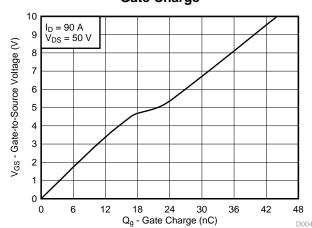
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT	
V_{DS}	Drain-to-Source Voltage	100	٧	
V_{GS}	Gate-to-Source Voltage	±20	V	
	Continuous Drain Current (Package limited)	200		
I _D	Continuous Drain Current (Silicon limited), $T_C = 25^{\circ}C$	136	А	
	Continuous Drain Current (Silicon limited), $T_C = 100$ °C	98		
I_{DM}	Pulsed Drain Current (1)	400	Α	
P_D	Power Dissipation	250	W	
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 175	°C	
E _{AS}	Avalanche Energy, single pulse I_D = 72 A, L = 0.1 mH, R_G = 25 Ω	259	mJ	

(1) Max $R_{\theta JC} =$ 0.6° C/W, Pulse duration $\leq 100 \mu s$, Duty cycle ≤ 1%

Gate Charge



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4 Revision History

DATE	REVISION	NOTES
October 2015	*	Initial release.

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5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS		1	'	
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _D = 250 μA	100		V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 80 V		1	μA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 20 V		100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.2 2.6	3.2	V
<u> </u>	Danie to course on anietone	V _{GS} = 6 V, I _D = 90 A	5.3	6.6	mΩ
R _{DS(on)}	Drain-to-source on resistance	V _{GS} = 10 V, I _D = 90 A	4.6	5.6	mΩ
9 _{fs}	Transconductance	V _{DS} = 10 V, I _D = 90 A	113		S
DYNAM	IC CHARACTERISTICS		<u> </u>		
C _{iss}	Input capacitance		3890	5060	pF
C _{oss}	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	674	876	pF
C _{rss}	Reverse transfer capacitance		14	18	pF
R_G	Series gate resistance		1.3	2.6	Ω
Qg	Gate charge total (10 V)		44	57	nC
Q _{gd}	Gate charge gate to drain	V 50 V 1 00 A	5.6		nC
Q _{gs}	Gate charge gate to source	$V_{DS} = 50 \text{ V}, I_{D} = 90 \text{ A}$	17		nC
Q _{g(th)}	Gate charge at V _{th}		9.6		nC
Q _{oss}	Output charge	V _{DS} = 50 V, V _{GS} = 0 V	124		nC
t _{d(on)}	Turn on delay time		9		ns
t _r	Rise time	V _{DS} = 50 V, V _{GS} = 10 V,	3		ns
$t_{d(off)}$	Turn off delay time	$I_{DS} = 90 \text{ A}, R_G = 0 \Omega$	14		ns
t _f	Fall time		2		ns
DIODE (CHARACTERISTICS		<u>.</u>	'	
V _{SD}	Diode forward voltage	I _{SD} = 90 A, V _{GS} = 0 V	0.9	1.0	V
Q _{rr}	Reverse recovery charge	V _{DS} = 50 V, I _E = 90 A,	326		nC
t _{rr}	Reverse recovery time	di/dt = 300 A/μs	74		ns

5.2 Thermal Information

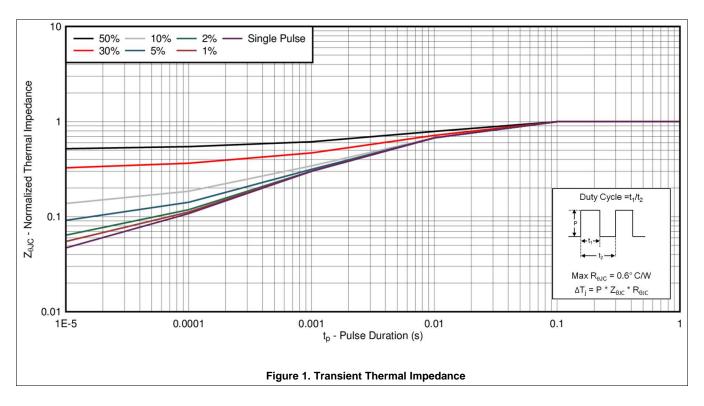
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

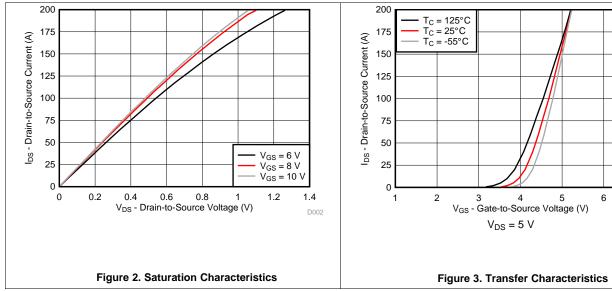
	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance			0.6	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance			62	°C/W

Product Folder Links: CSD19532KTT

5.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

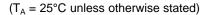


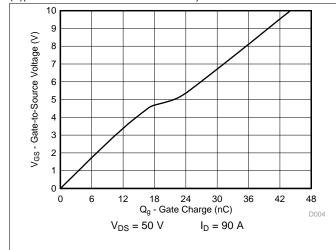




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Typical MOSFET Characteristics (continued)





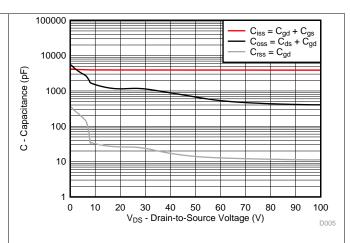


Figure 4. Gate Charge

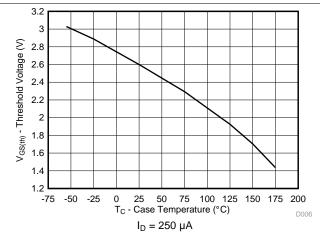


Figure 5. Capacitance

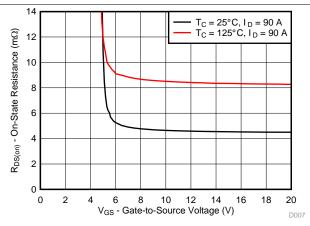


Figure 6. Threshold Voltage vs Temperature

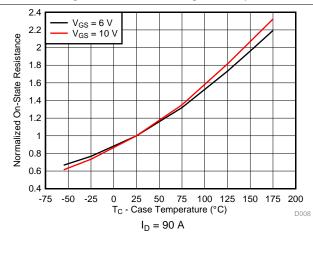


Figure 7. On-State Resistance vs Gate-to-Source Voltage

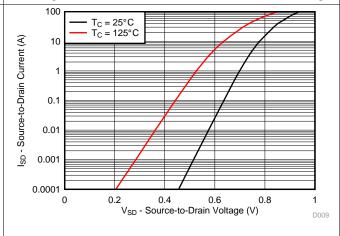


Figure 8. Normalized On-State Resistance vs Temperature

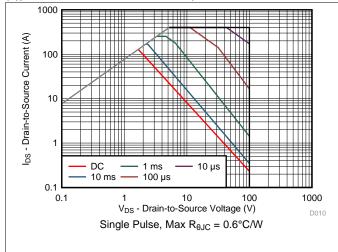
Figure 9. Typical Diode Forward Voltage

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Typical MOSFET Characteristics (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



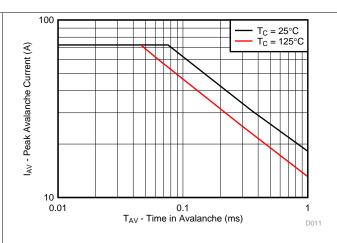


Figure 10. Maximum Safe Operating Area

Figure 11. Single Pulse Unclamped Inductive Switching

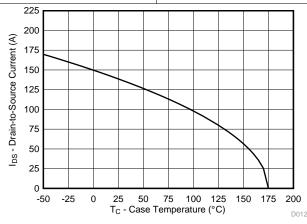


Figure 12. Maximum Drain Current vs Temperature

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6 Device and Documentation Support

6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.2 Trademarks

NexFET, E2E are trademarks of Texas Instruments.

All other trademarks are the property of their respective owners.

6.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

Product Folder Links: CSD19532KTT

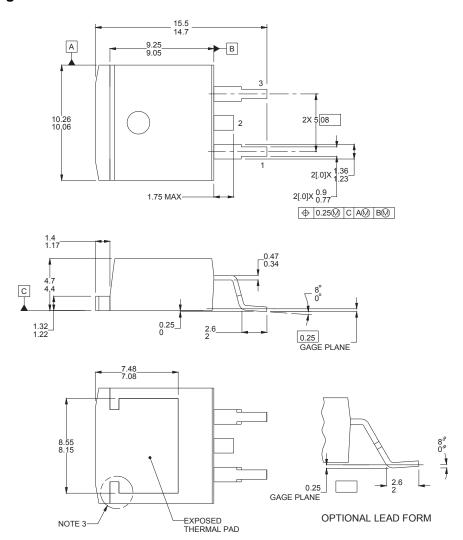
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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 KTT Package Dimensions



Notes:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. Features may not exist and shape may vary per different assembly sites.

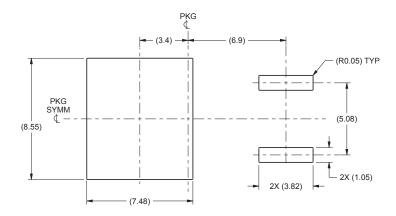
Pin Configuration

POSITION	DESIGNATION
Pin 1	Gate
Pin 2 / Tab	Drain
Pin 3	Source

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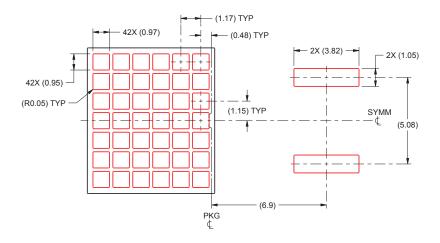
7.2 Recommended PCB Pattern





For recommended circuit layout for PCB designs, see application note SLPA005 - Reducing Ringing Through PCB Layout Techniques.

7.3 Recommended Stencil Opening (0.125 mm Stencil Thickness)



Notes:

- 1. This package is designed to be soldered to a thermal pad on the board. See application notes, PowerPAD Thermally Enhanced Package (SLMA002) and PowerPAD Made Easy (SLMA004) for more information.
- 2. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 3. Board assembly site may have different recommendations for stencil design.

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PACKAGE OPTION ADDENDUM

10-Nov-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD19532KTT	ACTIVE	DDPAK/ TO-263	KTT	3	500	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-55 to 175	CSD19532KTT	Samples
CSD19532KTTT	ACTIVE	DDPAK/ TO-263	KTT	3	50	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-55 to 175	CSD19532KTT	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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